

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 04-031396

(43)Date of publication of application : 03.02.1992

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(51)Int.Cl. C30B 25/14  
C30B 29/40  
C30B 29/42  
// H01L 21/205

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(21)Application number : 02-132514

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(22)Date of filing : 24.05.1990

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## (54) GROWTH OF SEMICONDUCTOR CRYSTAL

### (57)Abstract:

**PURPOSE:** To form a monomolecular layer of atomic layer epitaxy in a short time in forming a thin film of semiconductor single crystal from two or more kinds of constituent elements by forming a substantial part of film thickness from low-temperature thermally decomposable raw materials and the rest of the film from raw materials decomposable at a higher temperature.

**CONSTITUTION:** Raw materials of two or more kinds of constituent elements are alternately fed by an atomic layer epitaxy, a thin film of semiconductor single crystal is grown by each mono-atomic layer and piled to form semiconductor crystal. In the operation, for example, in growing a thin film of single crystal of GaAs, a mono-atomic layer of Ga is formed from a trialkylgallium except trimethylgallium and trimethylgallium and a mono-atomic layer of As is formed from arsine. Consequently, time required for formation of a monomolecular layer by atomic epitaxy is extremely shortened.

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## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

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